

CMPTA77

**SURFACE MOUNT
PNP SILICON
DARLINGTON TRANSISTOR**



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTA77 type is a PNP Silicon Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

MARKING CODE: C77

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CES} 60
 V_{EBO} 10
 I_C 500
 P_D 350
 T_J, T_{stg} -65 to +150
 Θ_{JA} 357

UNITS

V
V
mA
mW
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=50\text{V}$		500	nA
I_{CBO}	$V_{CB}=50\text{V}$		100	nA
I_{EBO}	$V_{EB}=10\text{V}$		100	nA
BV_{CES}	$I_C=100\mu\text{A}$	60		V
BV_{CBO}	$I_C=100\mu\text{A}$	60		V
$V_{CE(SAT)}$	$I_C=100\text{mA}$, $I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}$, $I_C=100\text{mA}$		2.0	V
h_{FE}	$V_{CE}=5.0\text{V}$, $I_C=10\text{mA}$	10,000		
h_{FE}	$V_{CE}=5.0\text{V}$, $I_C=100\text{mA}$	10,000		
f_T	$V_{CE}=5.0\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	125		MHz

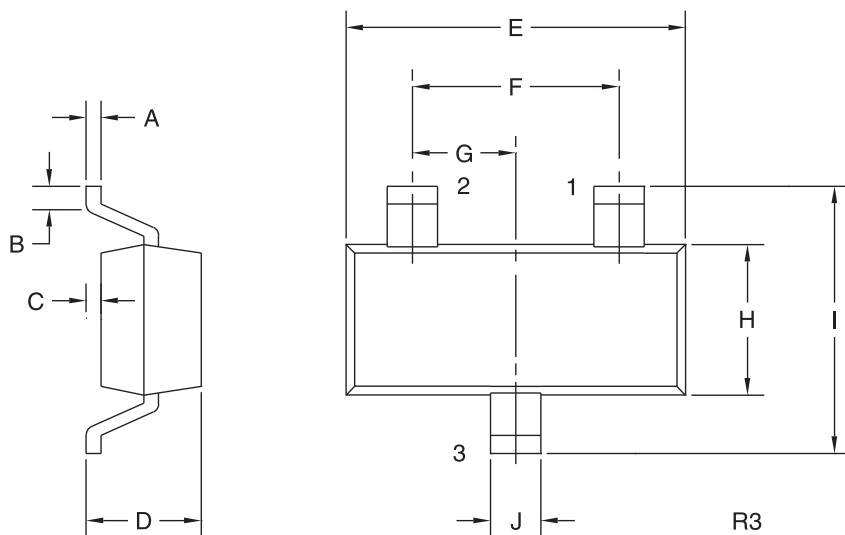
R1 (3-February 2010)

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C77

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (3-February 2010)